

Types HCT802, HCT802TX, HCT802TXV

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless specified otherwise)

Symbol	Parameters	Device B=Both	Min	Max	Units	Test Conditions
B_{VDSS}	Drain-Source Breakdown	B	90*		V	$I_D = 10\ \mu\text{A}^*$, $V_{GS} = 0$
V_{TH}	Gate Threshold Voltage	N	0.75	2.5	V	$V_{GS} = V_{DS}$, $I_D = 1\ \text{mA}$
		P	-2.0	-4.5	V	$I_D = -1\ \text{mA}$
I_{GSS}	Gate-Body Leakage	B		± 100	nA	$V_{GS} = \pm 20\ \text{V}$, $V_{DS} = 0$
I_{DSS}	Zero Gate Voltage Drain Current	B		10*	μA	$V_{DS} = 90\ \text{V}^*$, $V_{GS} = 0\ \text{V}$
		B		500*	μA	$T_j = 150^\circ\text{C}$
$I_{D(on)}$	On-State Drain Current	N	1.5		A	$V_{DS} = 25\ \text{V}$, $V_{GS} = 10\ \text{V}$
		P	-1.1		A	$V_{DS} = -15\ \text{V}$, $V_{GS} = -10\ \text{V}$
$R_{DS(on)}$	Drain-Source on Resistance	B		5	Ω	$V_{GS} = 10\ \text{V}^*$, $I_D = 1\ \text{A}^*$
G_{fs}	Forward Transconductance	N	170		mmho	$V_{DS} = 25\ \text{V}$, $I_D = 0.5\ \text{A}$
		P	200		mmho	$V_{DS} = -10\ \text{V}$, $I_D = -0.5\ \text{A}$
C_{iss}	Input Capacitance	N		70	pf	$V_{DS} = 25\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$
		P		150	pf	$V_{DS} = -25\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$
C_{oss}	Common Source Output Capacitance	N		40	pf	$V_{DS} = 25\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$
		P		60	pf	$V_{DS} = -25\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$
C_{rSS}	Reverse Transfer Capacitance	N		10	pf	$V_{DS} = 25\ \text{V}$, $V_{GS} = 0\ \text{A}$, $f = 1\ \text{MHz}$
		P		25	pf	$V_{DS} = -25\ \text{V}$, $V_{GS} = 0\ \text{A}$, $f = 1\ \text{MHz}$
$t_{(on)}$	Turn-on-time	N		15	ns	$V_{DD} = 25\ \text{V}$, $I_D = 1\ \text{A}$, $R_L = 50\ \Omega$
		P		50	ns	$V_{DD} = -25\ \text{V}$, $I_D = -0.5\ \text{A}$, $R_L = 50\ \Omega$
$t_{(off)}$	Turn-off-time	N		17	ns	$V_{DD} = 25\ \text{V}$, $I_D = 1\ \text{A}$, $R_L = 50\ \Omega$
		P		50	ns	$V_{DD} = -25\ \text{V}$, $I_D = -0.5\ \text{A}$, $R_L = 50\ \Omega$

* Reverse polarity for P-Channel device

HI-REL
SURFACE
MOUNT